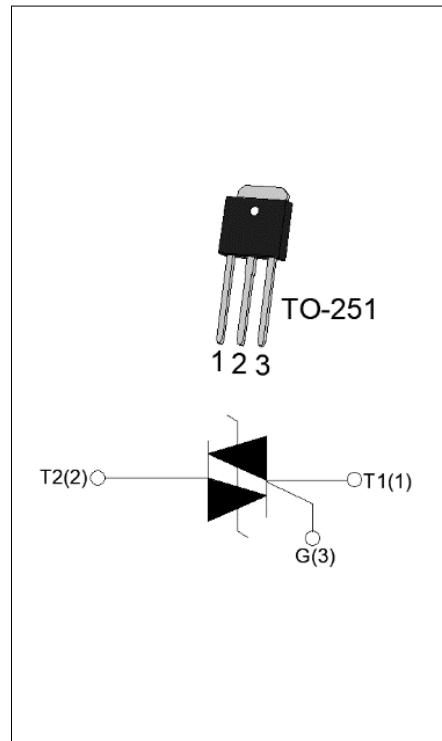


**DESCRIPTION:**

The ACJT210-6H triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT210-6H embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-251 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT\text{ I/II/III}}$	10/10/10	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c \leq 107^\circ\text{C}$ )	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		27.5	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	3.125	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$dI/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	2	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.1	W
Peak gate power	$P_{GM}$	10	W

Peak pulse voltage (T <sub>j</sub> =25°C; non-repetitive,off-state;FIG.7)	V <sub>PP</sub>	4.5	kV
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**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II - III	MAX.	10	mA
V <sub>GT</sub>		I - II - III	MAX.	1	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	I - II - III	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX.	25	mA
		II		35	
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX.	15	mA
dV/dt	V <sub>D</sub> =400V Gate Open T <sub>j</sub> =125°C		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=10V/μs, T <sub>j</sub> =125°C		MIN.	3	A/ms
t <sub>on</sub>	I <sub>G</sub> =20mA I <sub>A</sub> =200mA I <sub>R</sub> =20mA T <sub>j</sub> =25°C	TYP.	2.5	μs	
t <sub>off</sub>			25		
V <sub>CL</sub>	I <sub>CL</sub> =0.1mA t <sub>p</sub> =1ms		MIN.	700	V

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =3A t <sub>p</sub> =380μs	T <sub>j</sub> =25°C	1.5	V
V <sub>TO</sub>	Threshold voltage	T <sub>j</sub> =125°C	0.79	V
R <sub>D</sub>	Dynamic resistance	T <sub>j</sub> =125°C	242	mΩ
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	5	μA
I <sub>IRRM</sub>		T <sub>j</sub> =125°C	0.15	mA

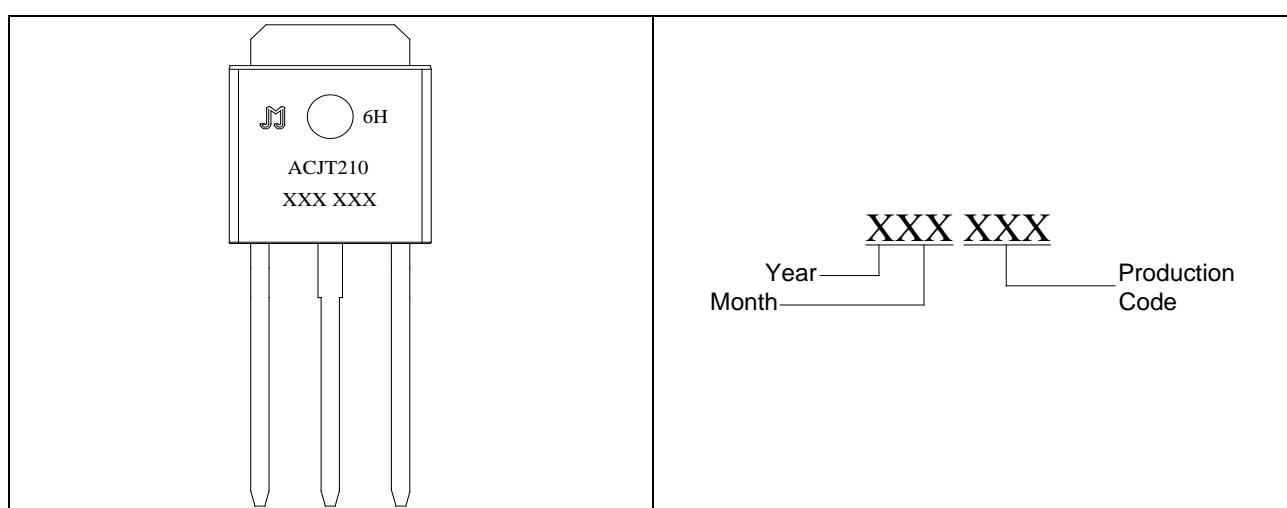
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	junction to case (AC)	6.5	°C/W
R <sub>th(j-a)</sub>	junction to ambient (AC)	145	°C/W

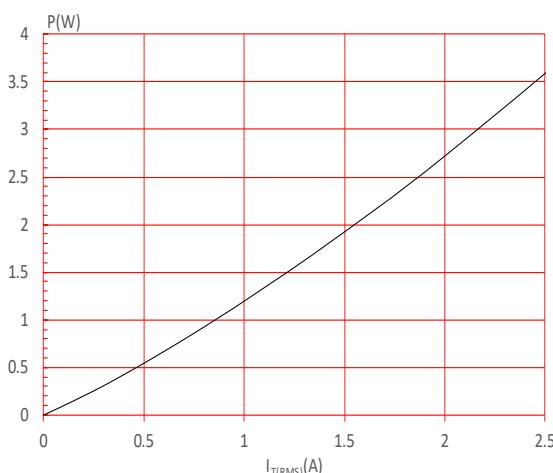
## ORDERING INFORMATION

AC	J	T	2	10	-6	H
AC switch						
JieJie Microelectronics Co.,Ltd.						
		Triacs				
			IT(RMS):2A			
				10: IGT1-3≤10mA		
						H:TO-251
					6:VDRM /VRRM≥600V	

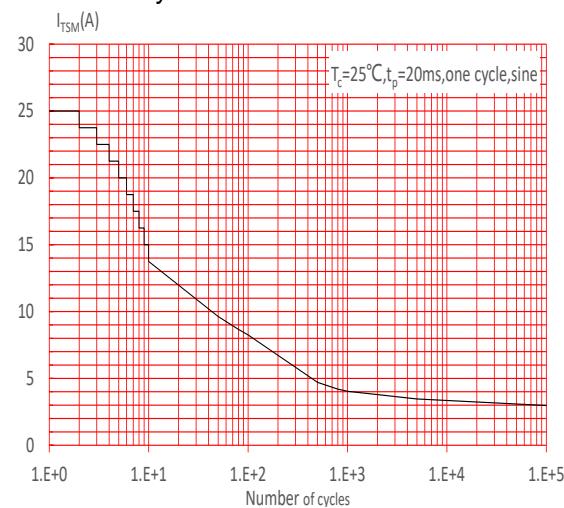
## MARKING



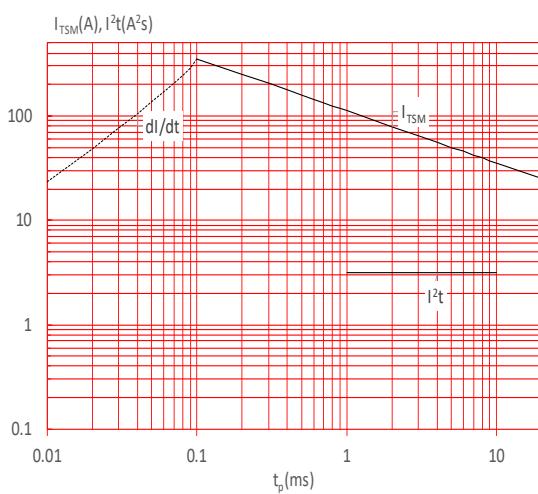
**FIG.1** Maximum power dissipation versus RMS on-state current



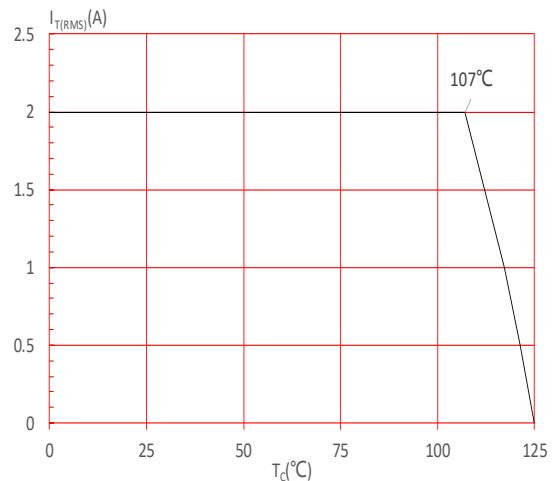
**FIG.3:** Surge peak on-state current versus number of cycles



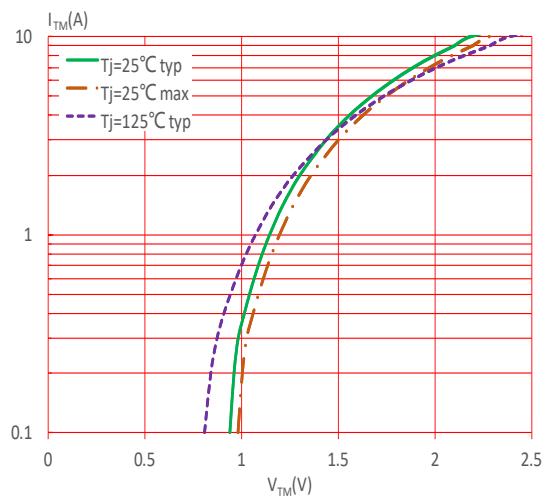
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

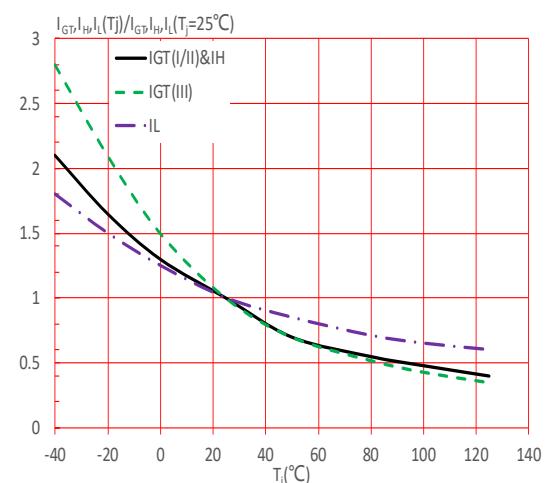
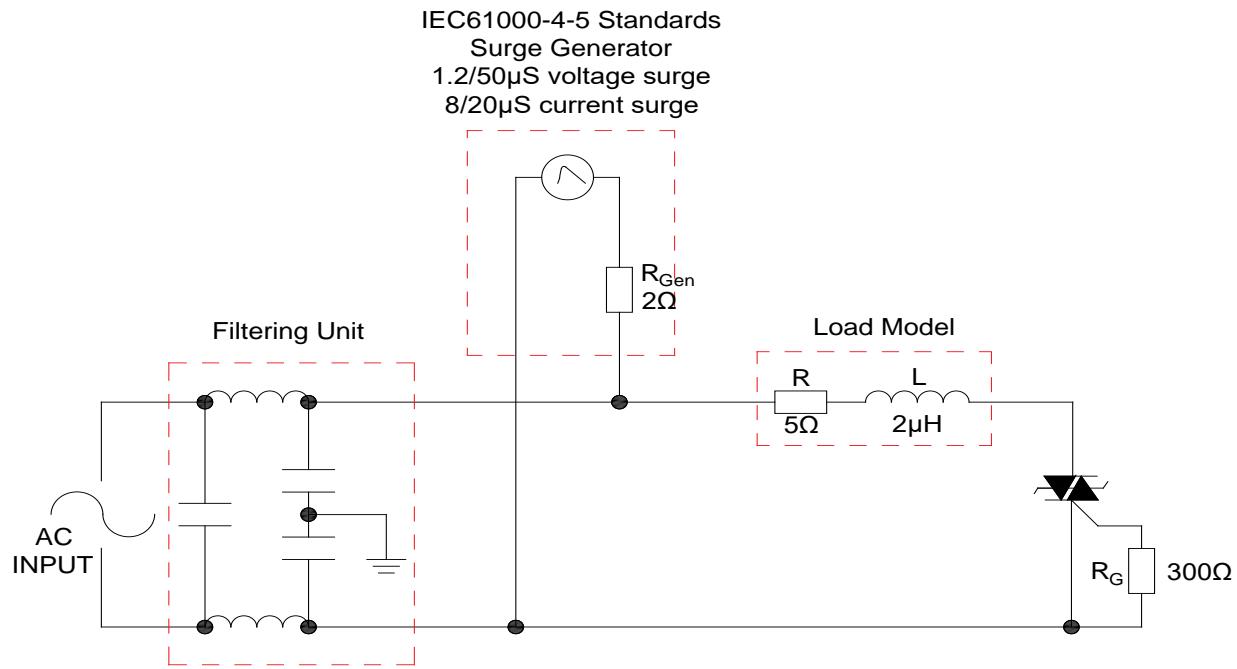


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

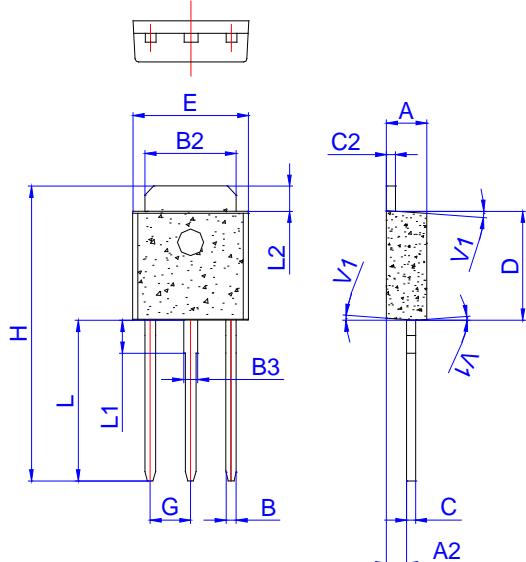
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT210-6H	600	10	TO-251	80	Tube

## Document Revision History

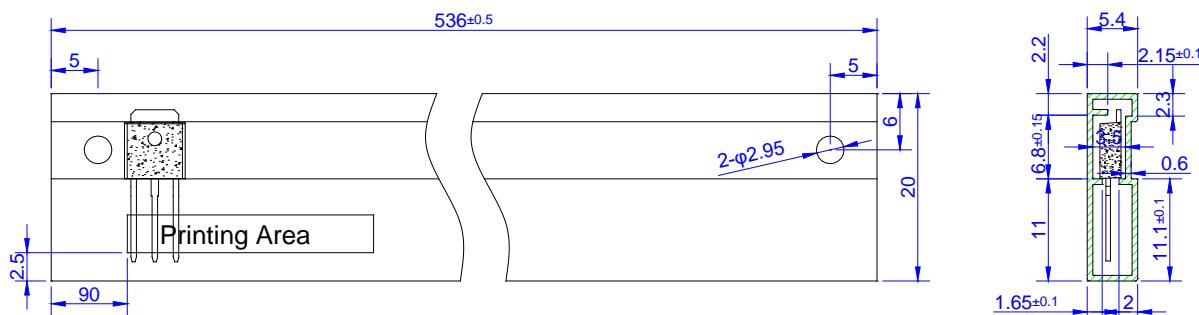
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1			4°			4°

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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